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Patent

UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Ping MEI, et al.

Examiner: H. Weiss

Serial No.: 09/934,548

Art Unit: 2814

Filed: August 23, 2001

Title: THIN FILM TRANSISTOR MEMORY DEVICE

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Technology Center 2000

BOX NON-FEE AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

AMENDMENT AND RESPONSE

Sir:

In response to the Office Action of September 11, 2002, please amend the above-identified application as follows:

In the Claims:

Please cancel claims 1-6 and 21-25 without prejudice or disclaimer.

Please amend claims 7 and 13 as follows:

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Amended 7. (Amended) A memory cell, comprising:
a diffusive metal;
at least one floating gate;
a gate insulator disposed between the at least one floating gate and the diffusive metal, wherein the gate insulator includes a conductive path;
a channel region coupled to the gate insulator;
a source coupled to the channel region; and
a drain coupled to the channel region, wherein the diffusive metal is responsive to a write voltage to diffuse conductive elements through the gate insulator.

Amended 13. (Amended) A memory array, comprising:
a substrate;
a plurality of gate lines disposed over the substrate;
a plurality of data lines crossing the gate lines and disposed over the substrate; and
a plurality of memory cells at crossing points of the gate lines and data lines, each